

ABSTRACT

Degradation of the n-value characteristics is suppressed while the J_c characteristics are improved. A substrate (32) having a single crystal structure, the main face (32B) of the substrate and a crystal face (32A) of the single crystal structure having an angle therebetween; an intermediate layer (34) formed on the main face (32B) of the substrate and having an axis oriented in a direction perpendicular to the crystal face (32A); and a superconducting layer (36) formed on the intermediate layer (34) and containing, as a main component, an oxide superconductor having a c-axis oriented in a direction perpendicular to the surface of the intermediate layer are included.